	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	6	lindert near nick.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:55
2	BRS	L2	36	justin near brask.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:56
3	BRS	L3	190	438/285.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
4	BRS	L4	2	3 and facet$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:57
5	BRS	L5	46881	facet$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:57
6	BRS	L7	0	(etch$3 or pattern$3) near15 (facet$3 near region$1) near25 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 13:58

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L6	39	(etch$3 or pattern$3) near15 (facet$3 near region$1) .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:04
8	BRS	L8	3410	(etch$3 or pattern$3) near15 (facet$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:04
9	BRS	L9	11	(etch$3 or pattern$3) near15 (sourece or drain) near15 (facet$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:07

	Type	L #	Hits	Search Text	DBs	Time Stamp
10	BRS	L10	32434	(etch$3 or pattern$3) near15 (sourece or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:07
11	BRS	L11	180	(etch$3 or pattern$3) near15 (source or drain) near15 (facet$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:12
12	BRS	L12	99377	(etch$3 or pattern$3) near15 (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:12

	Type	L #	Hits	Search Text	DBs	Time Stamp
13	BRS	L13	8770	(etch$3 or pattern$3) near15 (source/drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:12
14	BRS	L14	26	((etch$3 or pattern$3) near15 (source/drain)) near15 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:18
15	BRS	L15	237	((etch$3 or pattern$3) near15 (source or drain)) near15 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:18

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	110	((etch$3 or pattern$3) near5 (source or drain)) near15 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 14:48
17	BRS	L17	45	((remov$3) near5 (source or drain)) near15 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 15:06
18	BRS	L18	7	((remov$3) near5 (source/drain)) near15 (germanium or ge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/01/12 15:06

	U	1	Document ID	Title	Current OR
1			US 20040183142 A1	Semiconductor device and method of manufacturing the same	257/406
2			US 20030197224 A1	Methods for fabricating field effect transistors having elevated source/drain regions	257/348
3			US 20030025163 A1	Semiconductor device having elevated source/drain and method of fabricating the same	257/360
4			US 20020093099 A1	CONTACT PLUG	257/752
5			US 6737716 B1	Semiconductor device and method of manufacturing the same	257/406

	U	1	Document ID	Title	Current OR
6			US 6580134 B1	Field effect transistors having elevated source/drain regions	257/384
7			US 6469389 B2	Contact plug	257/752
8			US 6346447 B1	Shallow-implant elevated source/drain doping from a sidewall dopant source	438/300

	U	1	Document ID	Title	Current OR
9			US 6160299 A	Shallow-implant elevated source/drain doping from a sidewall dopant source	257/408
10			US 6060783 A	Self-aligned contact plugs	257/752

	U	1	Document ID	Title	Current OR
11			US 5858865 A	Method of forming contact plugs	438/585